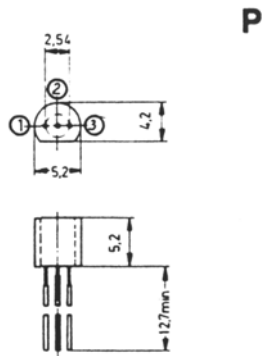


2SJ 111 (-GR..-V)
Silicon P-Channel JFET

Text: NF, ra, S
Complementary: 2SK369
Case: D9/a
Prod.:
Tos: Toshiba Electronics Europe GmbH

UDG: -25V
IG: -10mA
Ptot: 0,4W@Tu: 25°C
Tj: 125°C

Idss min: -5mA@UDS: -10V
Idss max: -30mA@UDS: -10V
UPmin: 0,3V@UDS: -10V ID: -0,1μA
UPmax: 2V@UDS: -10V ID: -0,1μA
|Yfs| min: 30mS@UDS: -10V ID: -1m
|Yfs| typ: 40mS@UDS: -10V ID: -1m
F: 1<2dB@UDS: -10V ID: -5m f: 1k
IGSS: 1nA@UGS: -25V

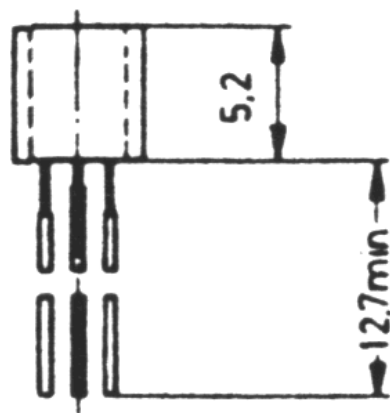
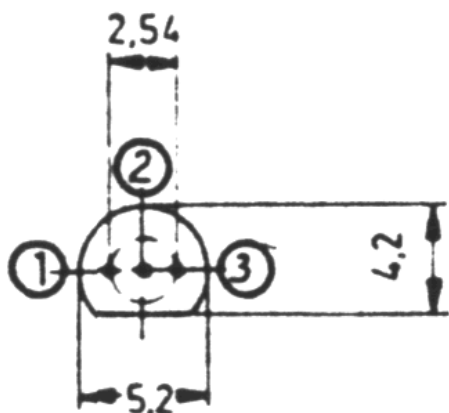


Pin1: Source
Pin2: Gate
Pin3: Drain

D9 (TO-92/SOT-30)

2SJ 111 (-GR.-V)
Silicon P-Channel JFET

P



D9

(TO-92/SOT-30)

Pin1: Source
Pin2: Gate
Pin3: Drain